STARPOWER

SEMICONDUCTOR **IGBT**

GD200FFA120C6S

1200V/200A 6 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

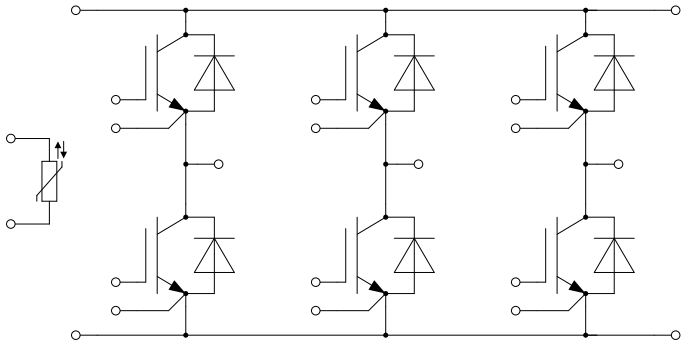
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- Short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology
- UL file number:E340089

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings T_C=25°C unless otherwise noted

IGBT

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ T_C=65°C	200	A
I_{CRM}	Repetitive Peak Collector Current t_p=1ms	400	A

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	200	A
I_{FRM}	Repetitive Peak Forward Current t_p=1ms	400	A

Module

Symbol	Description	Value	Unit
T_{vjmax}	Maximum Junction Temperature	175	°C
T_{vjop}	Operating Junction Temperature	-40 to +175	°C
T_{STG}	Storage Temperature Range	-40 to +125	°C
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	2500	V
d_{Creep}	Terminal to Heatsink	10.0	mm
d_{Clear}	Terminal to Heatsink	7.5	mm
CTI	Comperative Tracking Index	≥ 200	
RTI	RTI Elec. Housing	140	℃
Internal Isolation	Basic Insulation (class 1,IEC 61140)	Al_2O_3	

Note: T_{vjop} > 150°C is allowed for operation at overload conditions.

IGBT Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=200A,V_{GE}=15V, T_{vj}=25°C		1.50	1.95	V
		I_C=200A,V_{GE}=15V, T_{vj}=125°C		1.70		
		I_C=200A,V_{GE}=15V, T_{vj}=150°C		1.80		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=4.0mA,V_{CE}=V_{GE}, T_{vj}=25°C	5.4	6.2	7.0	V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_{vj}=25°C			50	uA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_{vj}=25°C			100	nA
R_{Gint}	Internal Gate Resistance			0.75		Ω
C_{ies}	Input Capacitance	V_{CE}=25V,f=1MHz, V_{GE}=0V		17.7		nF
C_{res}	Reverse Transfer Capacitance			0.13		nF
Q_G	Gate Charge	V_{GE}=-15…+15V		1.25		μC
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=200A, R_G=3.0Ω,L_S=35nH, V_{GE}=±15V,T_{vj}=25°C		200		ns
t_r	Rise Time			62		ns
$t_{d(off)}$	Turn-Off Delay Time			461		ns
t_f	Fall Time			222		ns
E_{on}	Turn-On Switching Loss			28.2		mJ
E_{off}	Turn-Off Switching Loss			17.9		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=200A, R_G=3.0Ω,L_S=35nH, V_{GE}=±15V,T_{vj}=125°C		226		ns
t_r	Rise Time			74		ns
$t_{d(off)}$	Turn-Off Delay Time			533		ns
t_f	Fall Time			316		ns
E_{on}	Turn-On Switching Loss			39.0		mJ
E_{off}	Turn-Off Switching Loss			23.7		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=200A, R_G=3.0Ω,L_S=35nH, V_{GE}=±15V,T_{vj}=150°C		230		ns
t_r	Rise Time			76		ns
$t_{d(off)}$	Turn-Off Delay Time			547		ns
t_f	Fall Time			337		ns
E_{on}	Turn-On Switching Loss			41.4		mJ
E_{off}	Turn-Off Switching Loss			24.5		mJ
I_{SC}	SC Data	t_P≤8μs,V_{GE}=15V, T_{vj}=150°C,V_{CC}=600V, V_{CEM}≤1200V		600		A

Diode Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	I_F=200A,V_{GE}=0V,T_{vj}=25°C		1.60	2.05	V
		I_F=200A,V_{GE}=0V,T_{vj}=125°C		1.65		
		I_F=200A,V_{GE}=0V,T_{vj}=150°C		1.65		
Q_r	Recovered Charge	V_R=600V,I_F=200A, -di/dt=3202A/μs,L_S=35nH, V_{GE}=-15V,T_{vj}=25°C		37.6		μC
I_{RM}	Peak Reverse Recovery Current			249		A
E_{rec}	Reverse Recovery Energy			11.3		mJ
Q_r	Recovered Charge	V_R=600V,I_F=200A, -di/dt=2729A/μs,L_S=35nH, V_{GE}=-15V,T_{vj}=125°C		58.9		μC
I_{RM}	Peak Reverse Recovery Current			264		A
E_{rec}	Reverse Recovery Energy			18.5		mJ
Q_r	Recovered Charge	V_R=600V,I_F=200A, -di/dt=2645A/μs,L_S=35nH, V_{GE}=-15V,T_{vj}=150°C		64.1		μC
I_{RM}	Peak Reverse Recovery Current			266		A
E_{rec}	Reverse Recovery Energy			20.2		mJ

NTC Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		kΩ
ΔR/R	Deviation of R_{100}	T_C=100 °C,R_{100}=493.3Ω	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15K))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15K))]$		3433		K

Module Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		21		nH
$R_{CC'+EE'}$	Module Lead Resistance,Terminal to Chip		1.80		mΩ
R_{thJC}	Junction-to-Case (per IGBT) Junction-to-Case (per Diode)			0.239 0.371	K/W
R_{thCH}	Case-to-Heatsink (per IGBT) Case-to-Heatsink (per Diode)		0.120 0.131		K/W
M	Mounting Torque, Screw:M5	3.0		6.0	N.m
G	Weight of Module		300		g

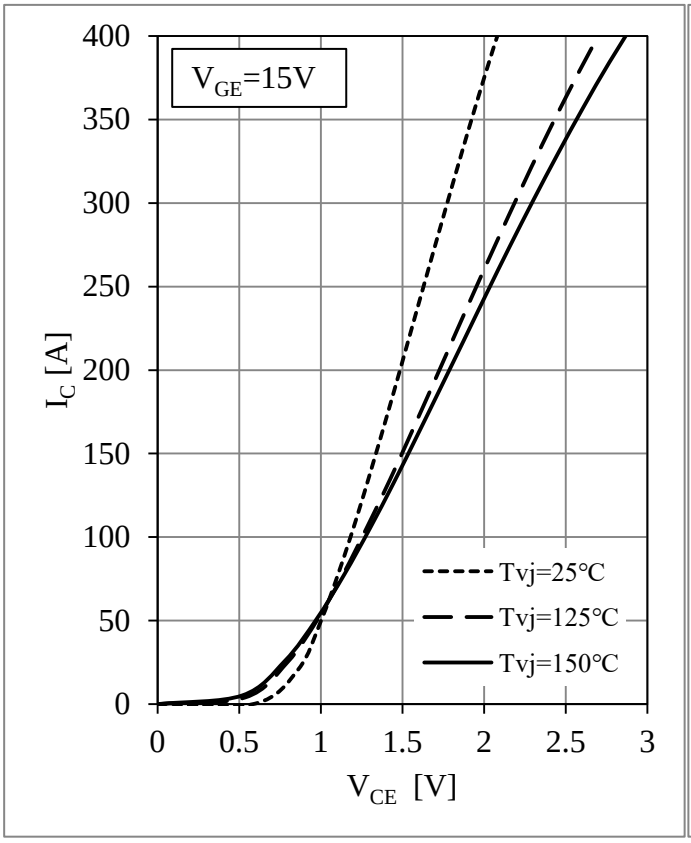


Fig 1. IGBT Output Characteristics

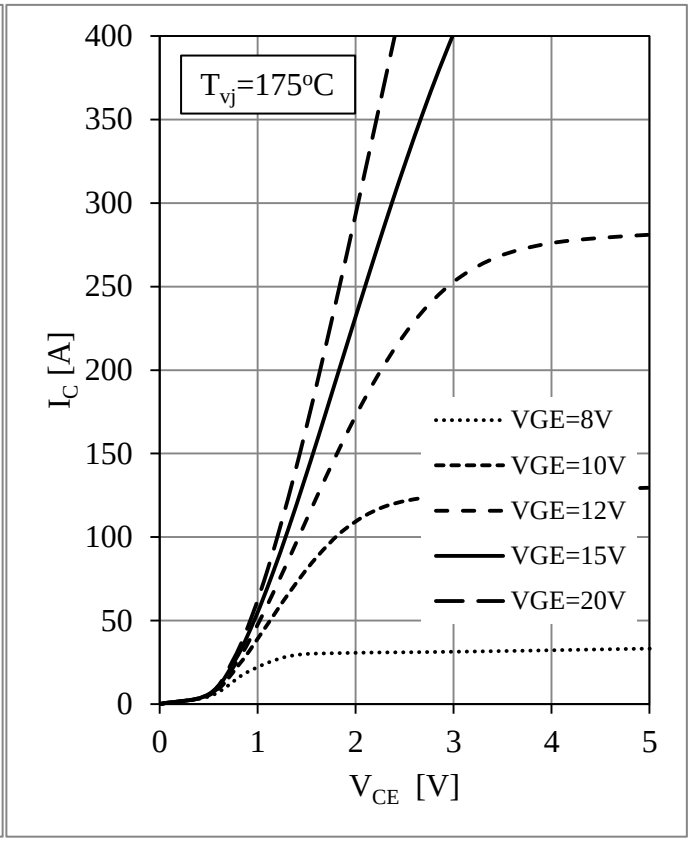


Fig 2. IGBT Output Characteristics

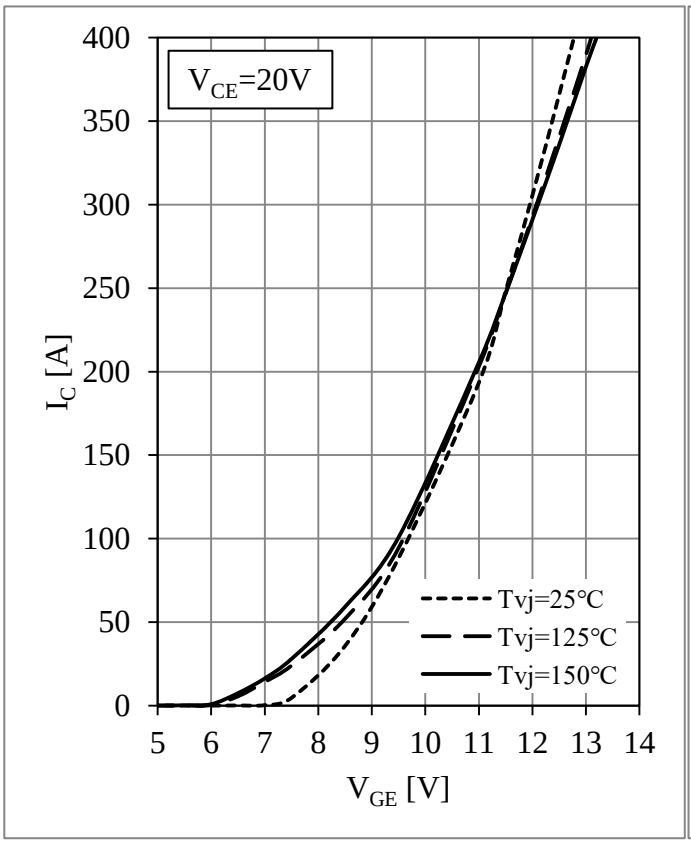


Fig 3. IGBT Transfer Characteristics

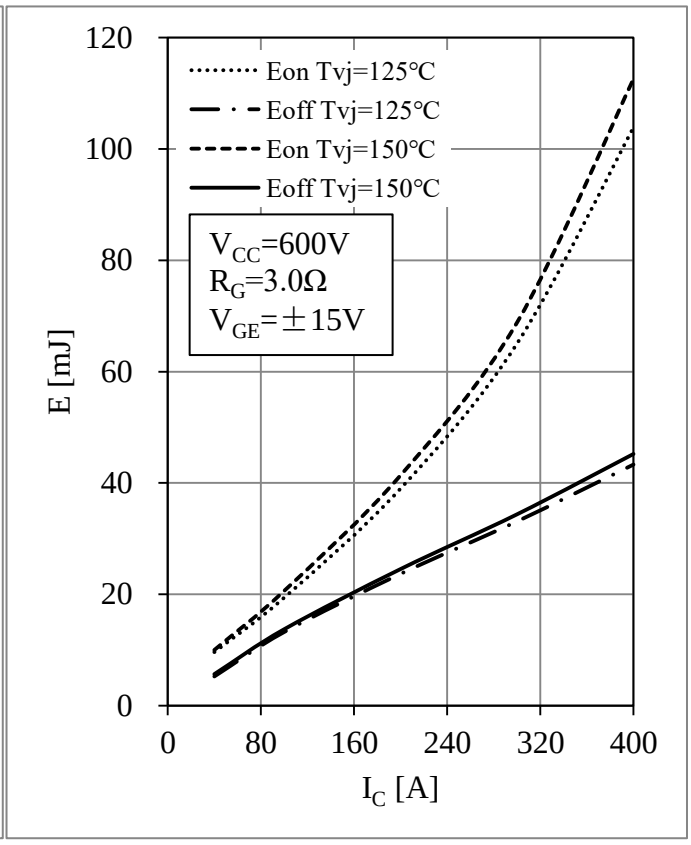


Fig 4. IGBT Switching Loss vs. I_C

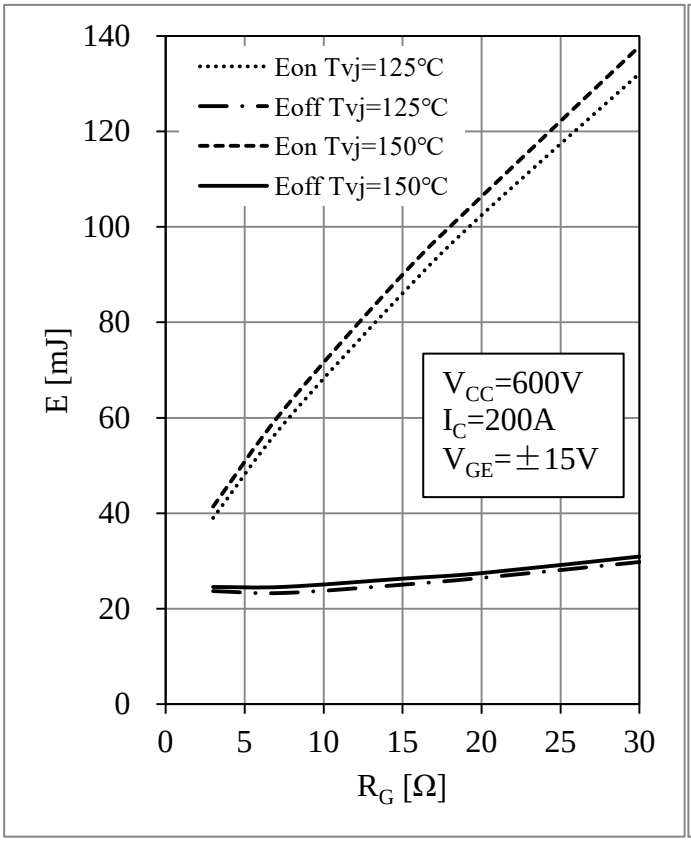


Fig 5. IGBT Switching Loss vs. R_G

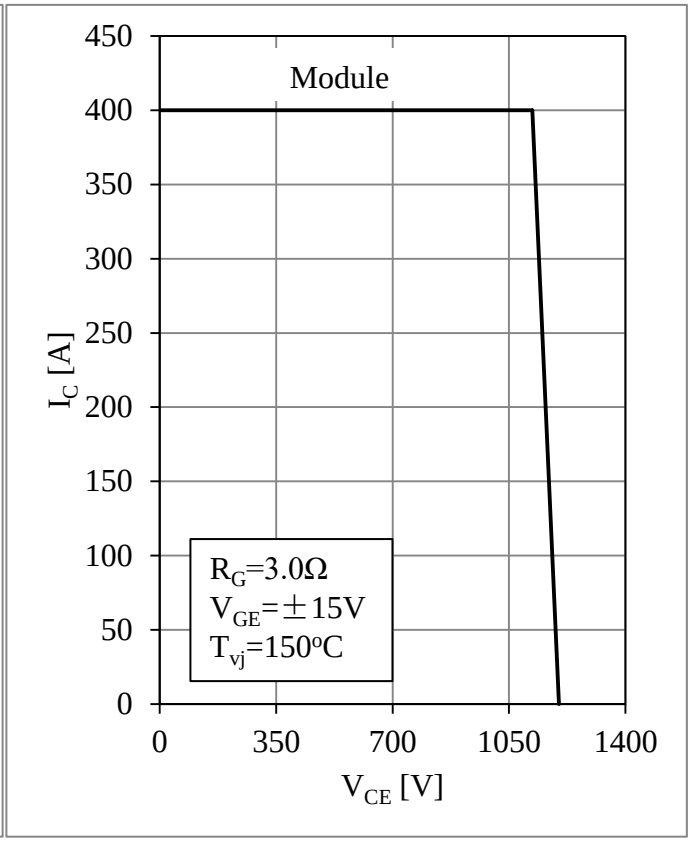


Fig 6. IGBT RBSOA

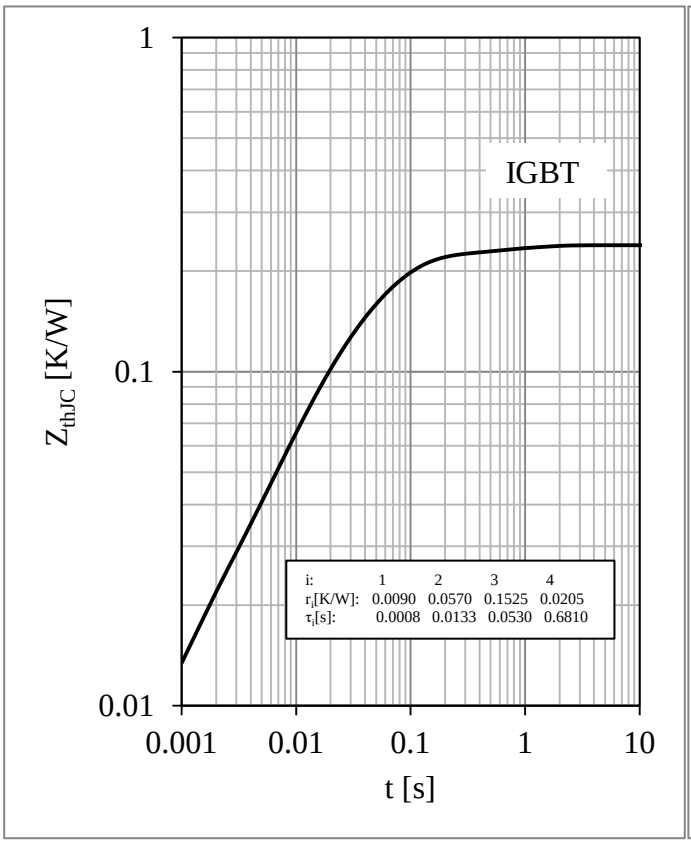


Fig 7. IGBT Transient Thermal Impedance

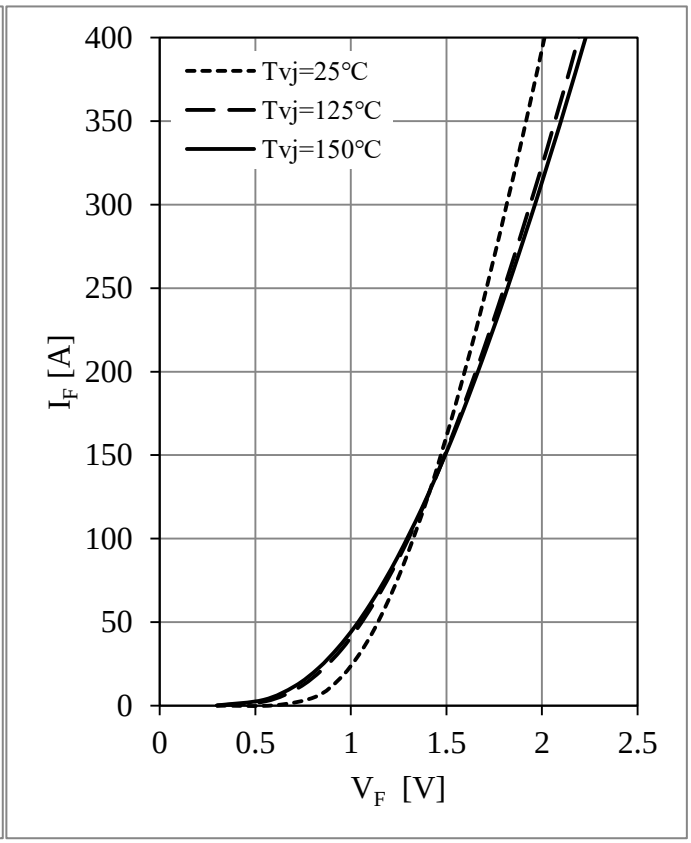


Fig 8. Diode Forward Characteristics

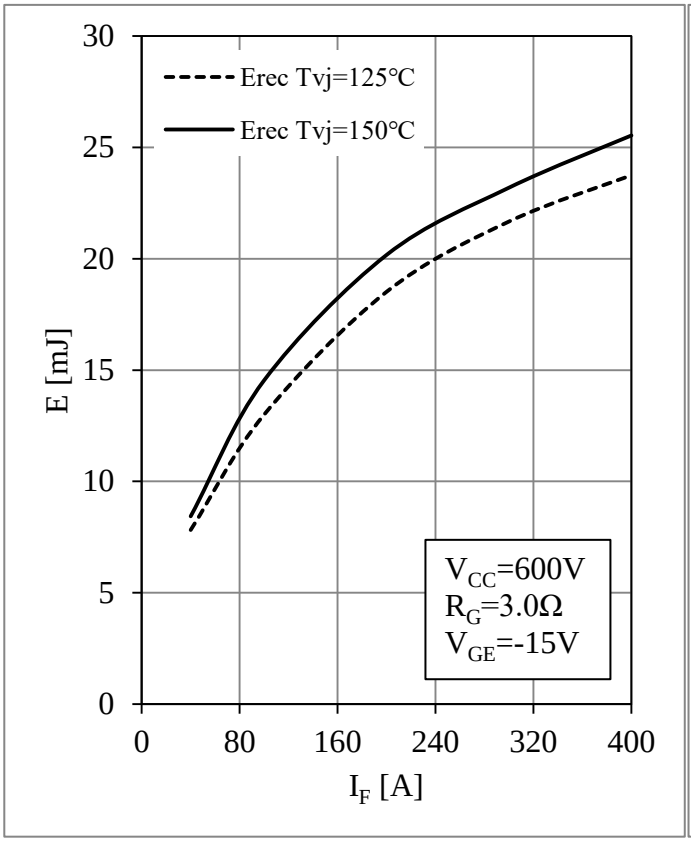


Fig 9. Diode Switching Loss vs. I_F

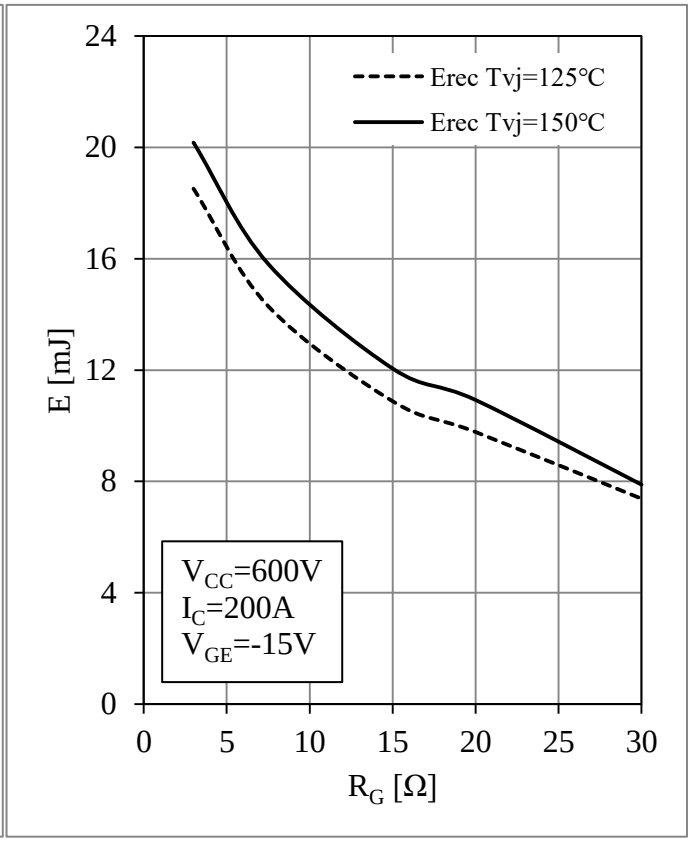


Fig 10. Diode Switching Loss vs. R_G

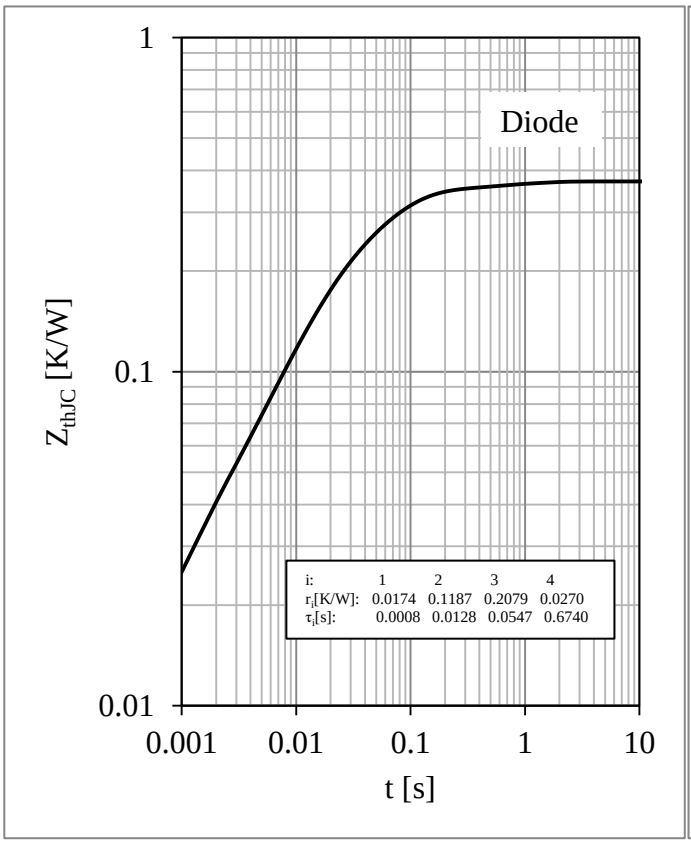


Fig 11. Diode Transient Thermal Impedance

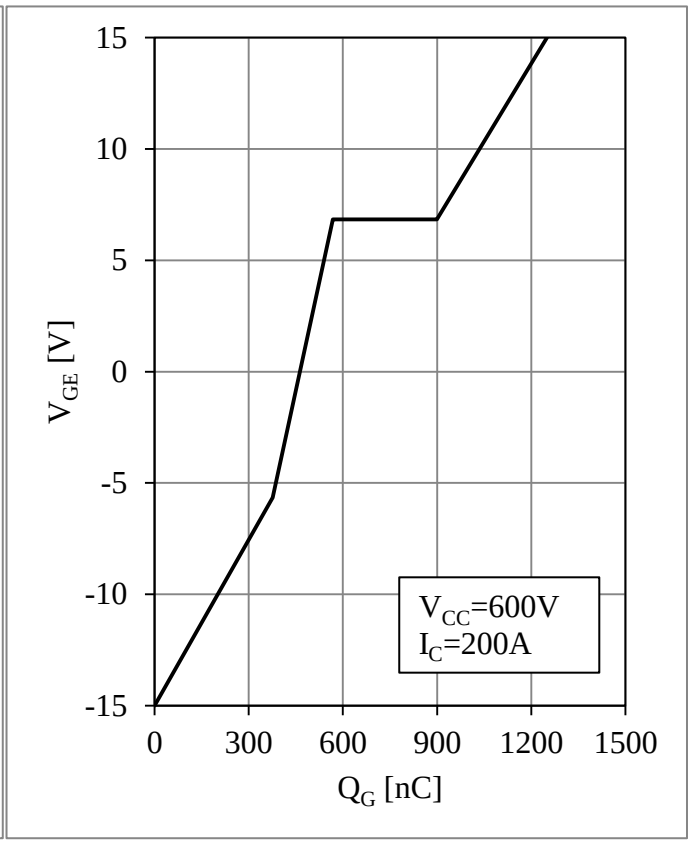


Fig 12. IGBT Gate Charge Characteristic

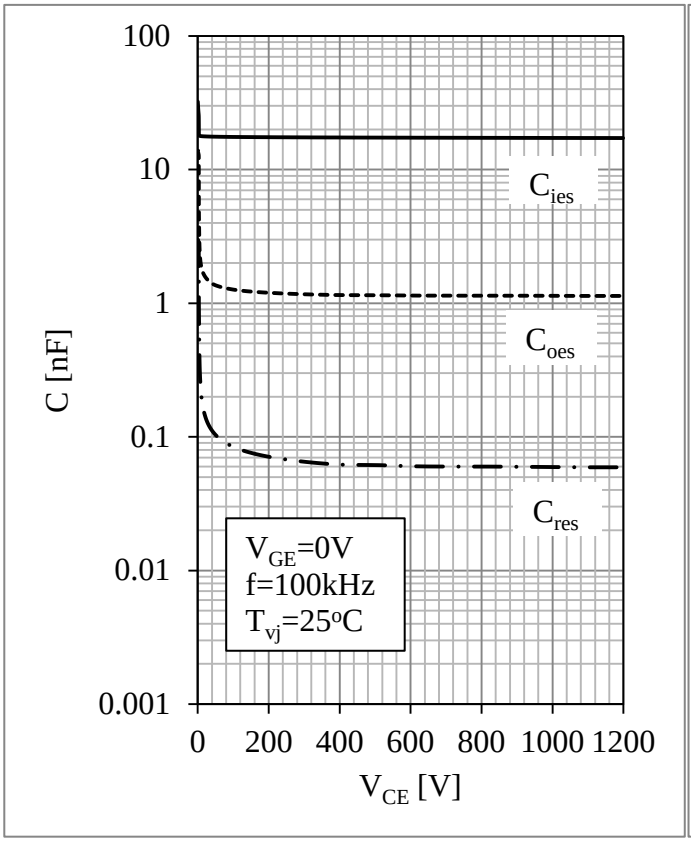


Fig 13. IGBT Capacity Charcteristic

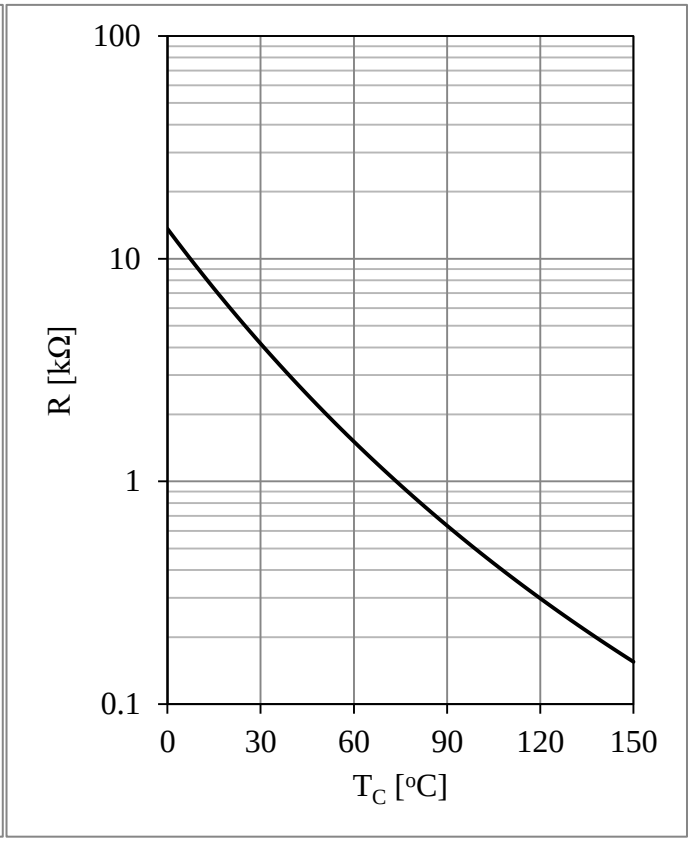
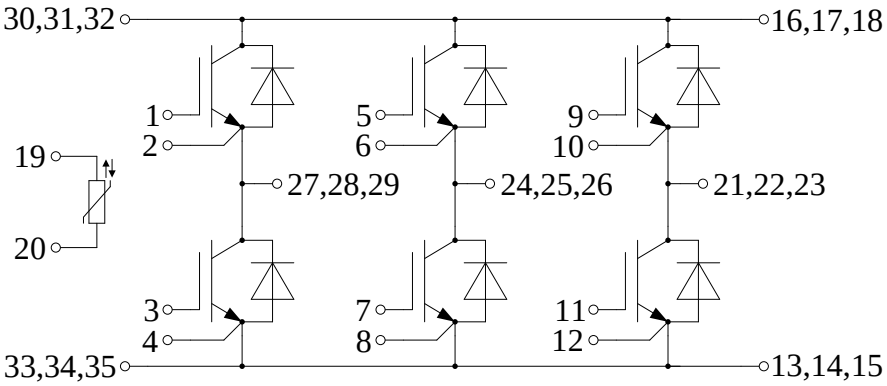


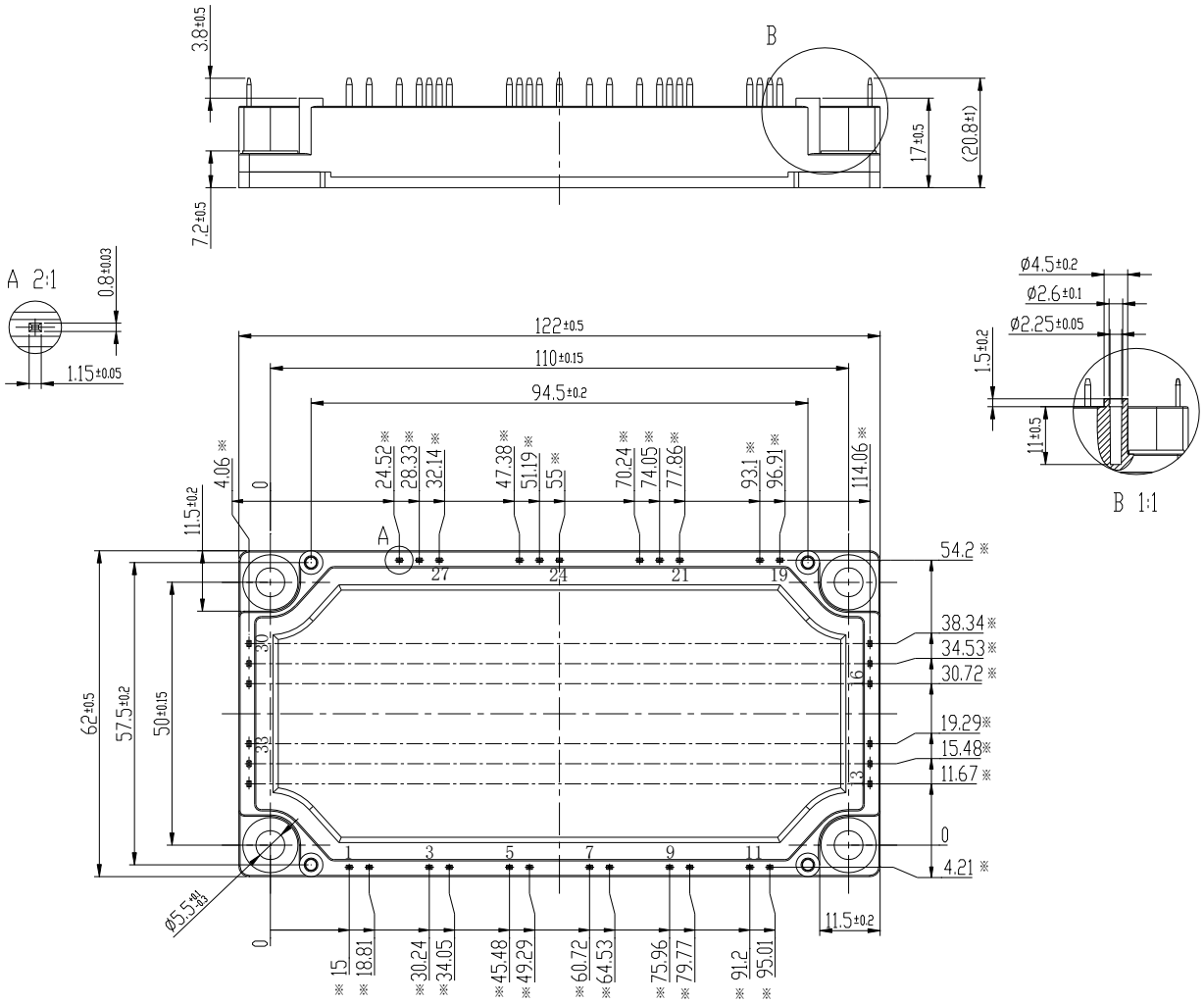
Fig 14. NTC Temperature Characteristic

Circuit Schematic

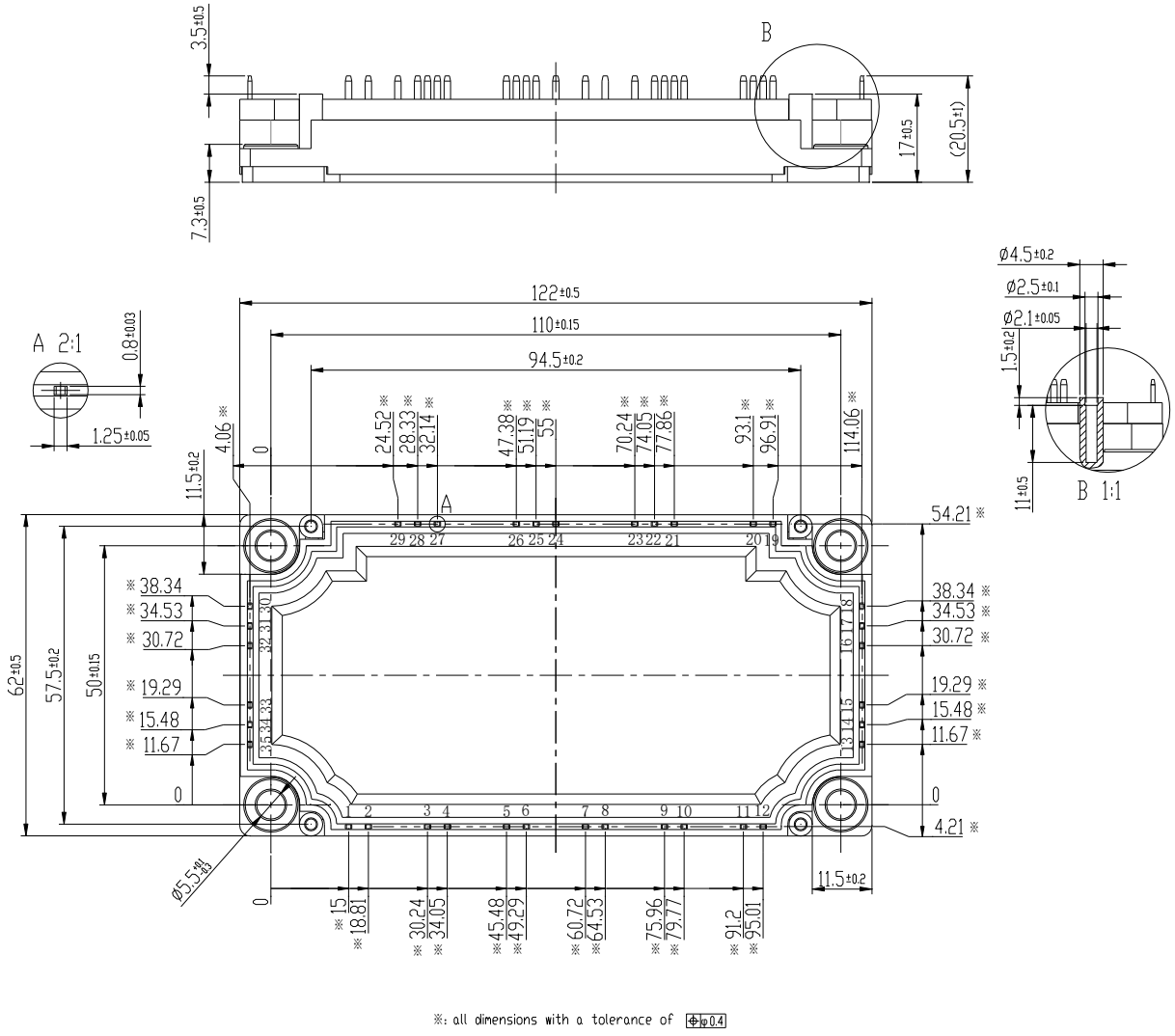


Package Dimensions

Dimensions in Millimeters



Black package



White package

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